50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

14 September 2018

Product data sheet

1. General description

NPN/PNP Resistor-Equipped double Transistors (RET) in a leadless ultra small DFN1412-6 (SOT1268) leadless Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PRMH11; PNP/PNP complement: PRMB11.

2. Features and benefits

- 100 mA output current capability
- · Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- Low package height of 0.5 mm
- AEC-Q101 qualified

3. Applications

- · Digital applications
- Cost-saving alternative to BC847/BC857 series in digital applications
- Control of IC inputs
- Switching loads

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor,	Per transistor, for the PNP transistor with negative polarity							
V _{CEO}	collector-emitter voltage	open base		-	-	50	V	
Io	output current			-	-	100	mA	
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 5 mA; T _{amb} = 25 °C		30	-	-		
R1	bias resistor 1	T _{amb} = 25 °C	[1]	7	10	13	kΩ	
R2/R1	bias resistor ratio		[1]	0.8	1	1.2		

[1] See section "Test information" for resistor calculation and test conditions.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	l1	input (base) TR1	1 7 6	
3	O2	output (collector) TR2	2 5	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	3 8 4	TR1 R2 R1
6	O1	output (collector) TR1		
7	O1	output (collector) TR1	Transparent top view	0.000
8	O2	output (collector) TR2	DFN1412-6 (SOT1268)	GND1 I1 O2 aaa-007379

6. Ordering information

Table 3. Ordering information

Type number	Package	age					
	Name	Description	Version				
PRMD3		plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 mm x 1.2 mm x 0.47 mm	SOT1268				

7. Marking

Table 4. Marking codes

Type number	Marking code
PRMD3	B3

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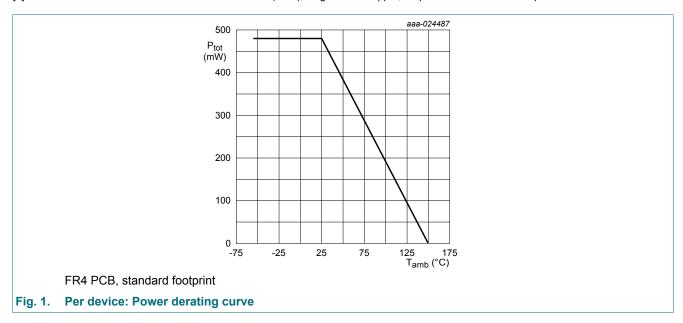
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or, for the PNP transistor wit	n negative polarity				
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	10	V
VI	input voltage	positive		-	40	V
		negative		-	-10	V
Io	output current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	480	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	261	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

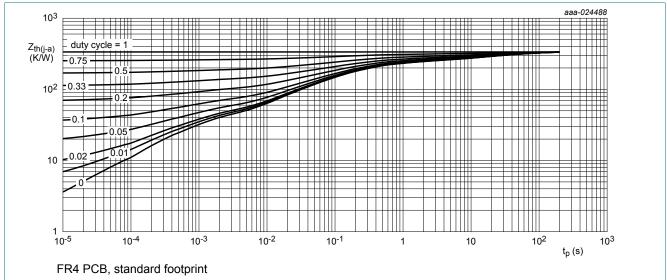


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or, for the PNP transistor v	vith negative polarity					
I _{CEO}		V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	1	μΑ
	current	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 150 °C		-	-	5	μΑ
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	400	μA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 5 mA; T _{amb} = 25 °C		30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	150	mV
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C		-	1.1	0.8	V
V _{I(on)}	on-state input voltage	V_{CE} = 0.3 V; I_{C} = 10 mA; T_{amb} = 25 °C		2.5	1.8	-	V
R1	bias resistor 1	T _{amb} = 25 °C	[1]	7	10	13	kΩ
R2/R1	bias resistor ratio		[1]	0.8	1	1.2	
C _C	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	2.5	pF
		V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	3	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	230	-	MHz
		V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	180	-	MHz

- [1] See section "Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor.

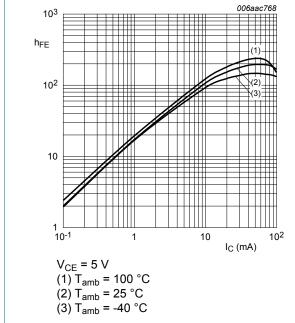


Fig. 3. NPN transistor: DC current gain as a function of collector current; typical values

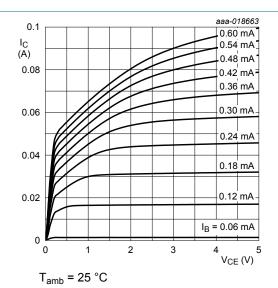
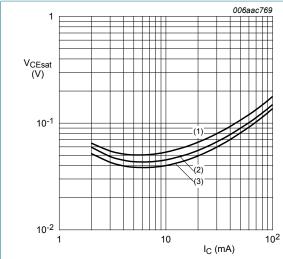


Fig. 4. NPN transistor: Collector current as a function of collector-emitter voltage; typical values

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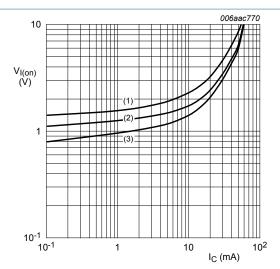


$$I_{\rm C}/I_{\rm B} = 20$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 5. **NPN** transistor: Collector-emitter saturation voltage as a function of collector current; typical values

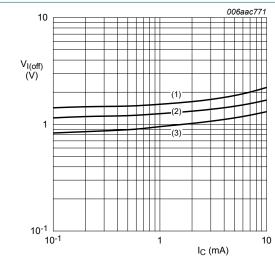


$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

NPN transistor: On-state input voltage as a Fig. 6. function of collector current; typical values



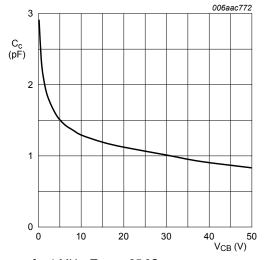
$$V_{CE} = 5 V$$

$$(1) T_{amb} = -40 °C$$

$$(2) T_{amb} = 25 °C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

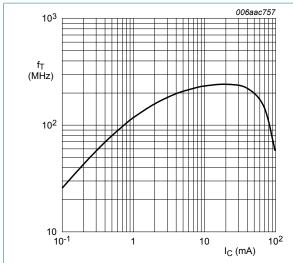
Fig. 7. NPN transistor: Off-state input voltage as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

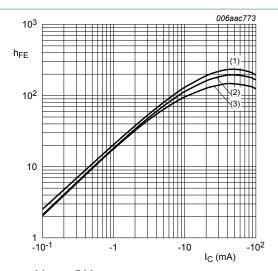
Fig. 8. NPN transistor: Collector capacitance as a function of collector-base voltage; typical

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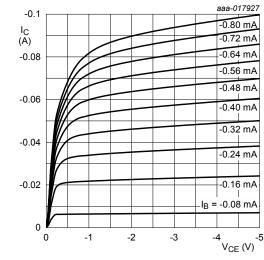
 V_{CE} = 5 V; T_{amb} = 25 °C

Fig. 9. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



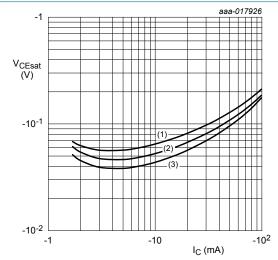
V_{CE} = -5 V (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 20$

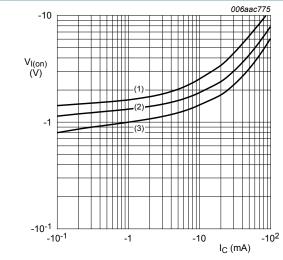
(1) T_{amb} = 100 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 12. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

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 V_{CE} = -0.3 V

(1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 13. PNP transistor: On-state input voltage as a function of collector current; typical values

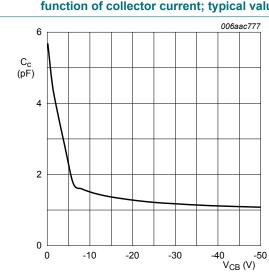
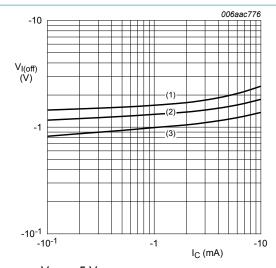


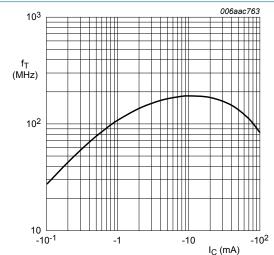
Fig. 15. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values

 $f = 1 MHz; T_{amb} = 25 °C$



V_{CE} = -5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 14. PNP transistor: Off-state input voltage as a function of collector current; typical values



 V_{CE} = -5 V; T_{amb} = 25 °C

Fig. 16. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

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11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

Resistor calculation

Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

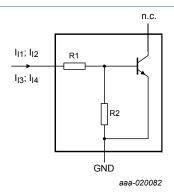


Fig. 17. NPN transistor: Resistor test circuit

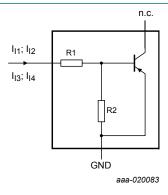


Fig. 18. PNP transistor: Resistor test circuit

Resistor test conditions

Table 8. Resistor test conditions

Per transistor; for the PNP transistor with negative polarity

R1 (kΩ)	R2 (kΩ)	Test conditions	st conditions					
		I _{I1}	I ₁₂	I ₁₃	I ₁₄			
10	10	350 μΑ	450 μA	-350 µA	-450 μA			

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12. Package outline

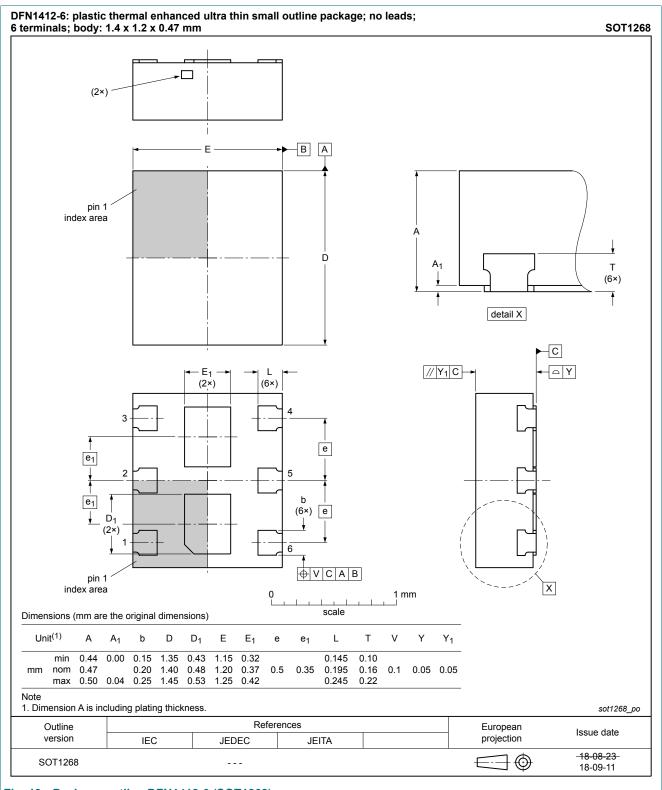
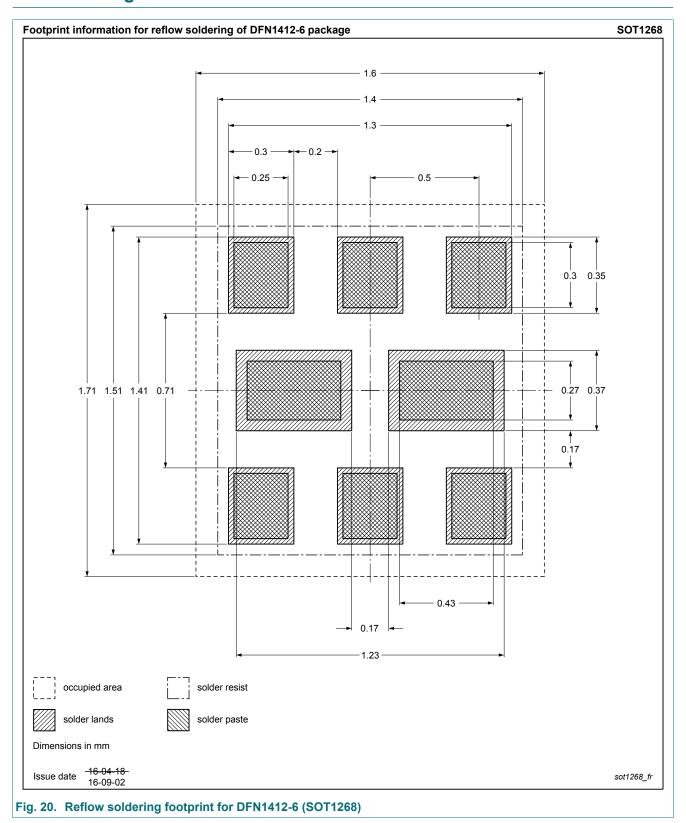


Fig. 19. Package outline DFN1412-6 (SOT1268)

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13. Soldering



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14. Revision history

Table 9. Revision history

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PRMD3 v.2	20180914	Product data sheet	-	PRMD3 v.1			
Modifications:	Package outline draw	Package outline drawing updated: Unit T added					
PRMD3 v.1	20170615	Product data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PRMD3

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